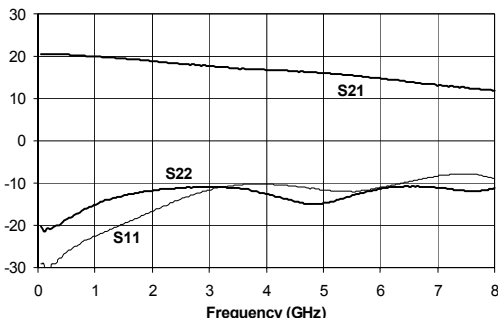


Product Description

Sirenza Microdevices' SBW-5089 is a high performance InGaP/GaAs Heterojunction Bipolar Transistor MMIC Amplifier. A Darlington configuration designed with InGaP process technology provides broadband performance up to 8 GHz with excellent thermal performance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Only a single positive supply voltage, DC-blocking capacitors, a bias resistor, and an optional RF choke are required for operation.

Gain & Return Loss Vs. Frequency

See App Circuit Page 6



SBW-5089

DC-8 GHz, Cascadable InGaP/GaAs HBT MMIC Amplifier



Product Features

- Wideband Flat Gain to 3GHz: +/-1.4dB
- P1dB = 13.4 @ 6GHz
- Input / Output VSWR < 2:3 to 8GHz
- Operates From Single Supply
- Low Thermal Resistance
- Darlington Configuration

Applications

- Wideband Instrumentation
- Fiber Optic Driver
- OC-48
- Basestation
- SAT COM

Symbol	Parameter	Units	Frequency	Min.	Typ.	Max.
G	Small Signal Gain (PC board and connector losses de-embedded)	dB	850 MHz 3000 MHz 4200 MHz 6000 MHz	19.3 17.0 16.2 14.5	20.3 18.0 17.2 15.5	21.3 19.0 18.2 16.5
P _{1dB}	Output Power at 1dB Compression	dBm	850 MHz 1950 MHz	18.4	20.1 19.4	
OIP ₃	Output Third Order Intercept Point	dBm	850 MHz 1950 MHz	32.0	35.5 34.0	
P _{out}	Output Power @ -45dBc ACP IS-95 9 Forward Channels	dBm	1950MHz		13.0	
Bandwidth	Determined by Return Loss (>10dB)	MHz			6000	
IRL	Worst case Input Return Loss	dB	DC-6000MHz	7	10	
ORL	Worst case Output Return Loss	dB	DC-6000MHz	8	11	
NF	Noise Figure	dB	1950 MHz		3.9	4.4
V _D	Device Operating Voltage	V		4.5	4.9	5.3
I _D	Device Operating Current	mA		72	80	88
R _{TH, j-l}	Thermal Resistance (junction to lead)	°C/W			97	

Test Conditions: V_S = 8 V, I_D = 80 mA Typ., OIP₃ Tone Spacing = 1 MHz, P_{out} per tone = 0 dBm
R_{BIAS} = 39 Ohms, T_L = 25°C, Z_S = Z_L = 50 Ohms

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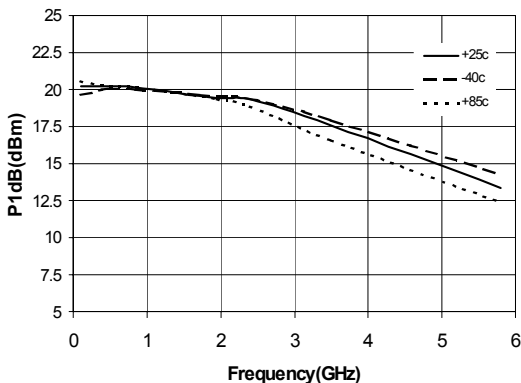
Typical RF Performance at Key Operating Frequencies

Symbol	Parameter	Unit	Frequency (MHz)					
			500	850	1950	2400	3500	5800*
G	Small Signal Gain	dB	20.5	20.3	19.1	18.7	17.3	15.1
OIP ₃	Output Third Order Intercept Point	dBm	36.5	35.5	34.0	33.0	30.5	25.5
P _{1dB}	Output Power at 1dB Compression	dBm	20.2	20.1	19.4	19.4	17.5	13.4
IRL	Input Return Loss	dB	26	26	19	15	12	12.5
ORL	Output Return Loss	dB	19	17.5	12	11	10.5	10.9
S ₂₁	Reverse Isolation	dB	22	23	23	23	23	23
NF	Noise Figure	dB	3.6	3.6	3.9	3.9	4.1	4.3

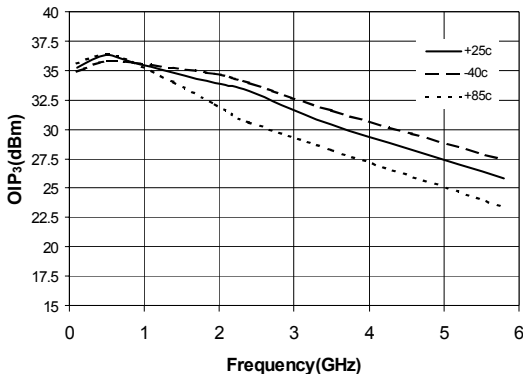
Test Conditions: $V_S = 8\text{ V}$ $I_D = 80\text{ mA Typ.}$ OIP₃ Tone Spacing = 1 MHz, P_{out} per tone = 0dBm
 $R_{BIAS} = 39\text{ Ohms}$ $T_L = 25^\circ\text{C}$ $Z_S = Z_L = 50\text{ Ohms}$ Basic Application Circuit

*NOTE: 5.8GHz data measured with tuned app circuit

P1dB vs. Frequency



OIP₃ vs. Frequency



Absolute Maximum Ratings

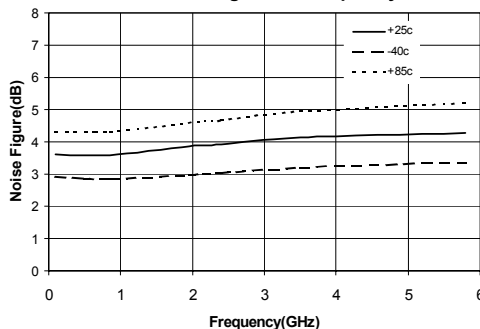
Parameter	Absolute Limit
Max. Device Current (I_D)	130 mA
Max. Device Voltage (V_D)	6 V
Max. RF Input Power	+17 dBm
Max Operating Dissipated Power	0.65 W
Max. Junction Temp. (T_J)	+150°C
Operating Temp. Range (T_L)	-40°C to +85°C
Max. Storage Temp.	+150°C
ESD	Class 1C

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression:

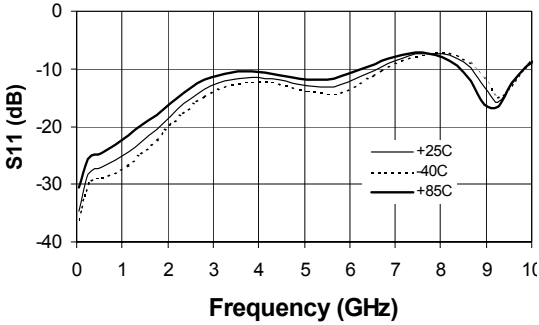
$$I_D V_D < (T_J - T_L) / R_{TH} \text{ J} \quad T_L = T_{LEAD}$$

Noise Figure vs. Frequency

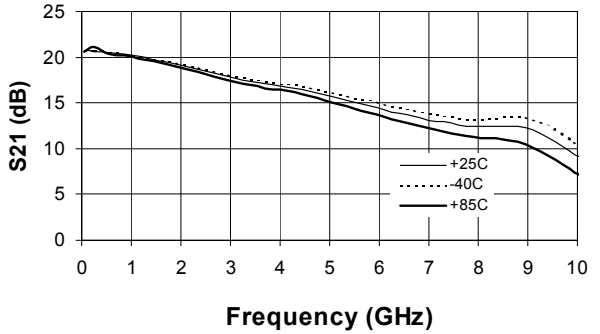


Test conditions: Bias Tee, Id=80mA, Vsup ply=8V, 39ohm drop resistor
 Basic App Circuit page 5

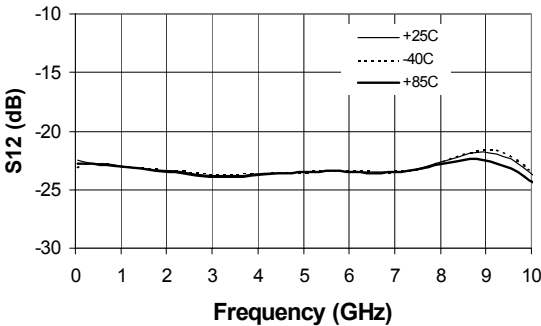
$|S_{11}|$ vs. Frequency



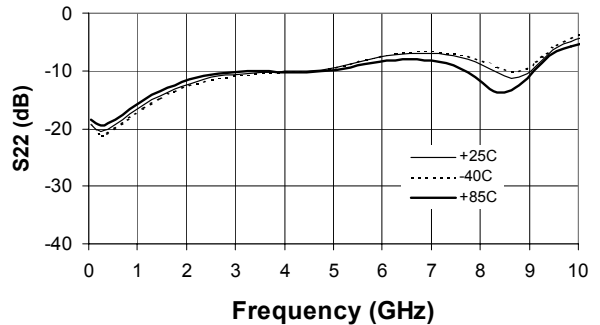
$|S_{21}|$ vs. Frequency



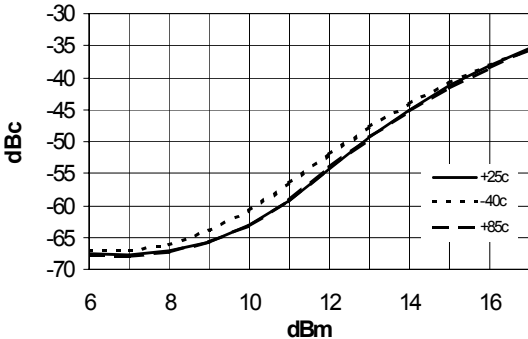
$|S_{12}|$ vs. Frequency



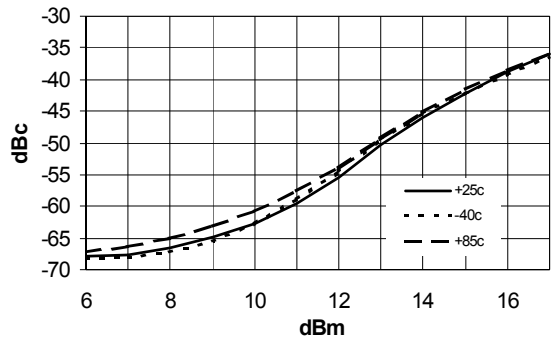
$|S_{22}|$ vs. Frequency



IS-95 @ 850MHz
 Adj. Channel Pwr. vs. Channel output Pwr.

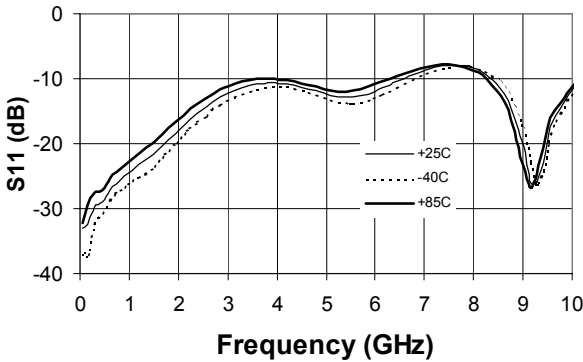


IS-95 @ 1950MHz
 Adj. Channel Pwr. vs. Channel Output Power

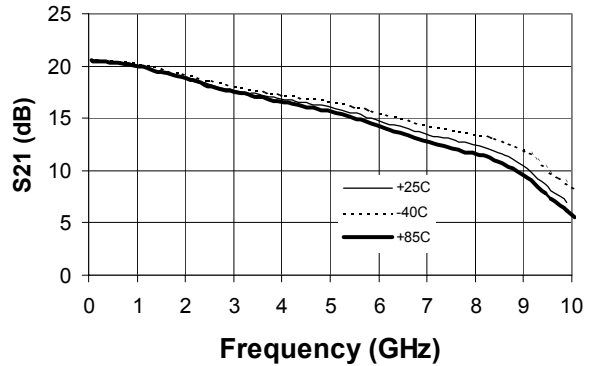


Test conditions: Bias Tee, $I_d=80\text{mA}$, $V_{\text{supply}}=8\text{V}$, 39ohm drop resistor
 Tuned Circuit Application with broadband bias tee page 6

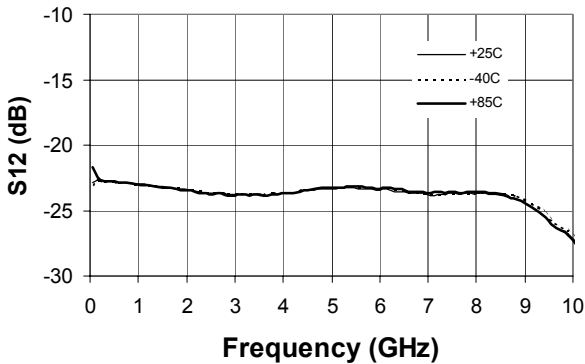
$|S_{11}|$ vs. Frequency



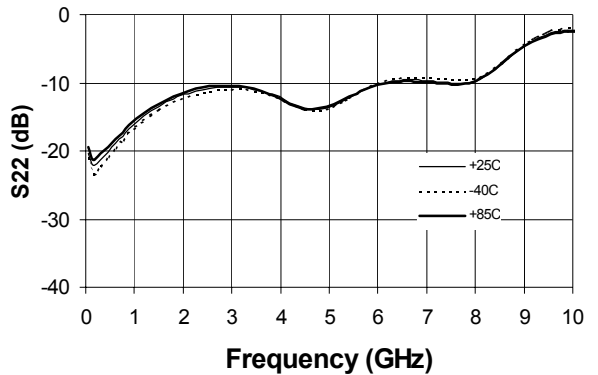
$|S_{21}|$ vs. Frequency



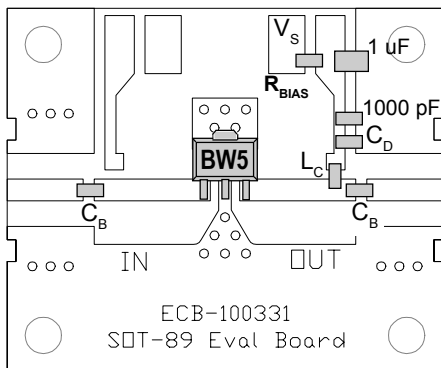
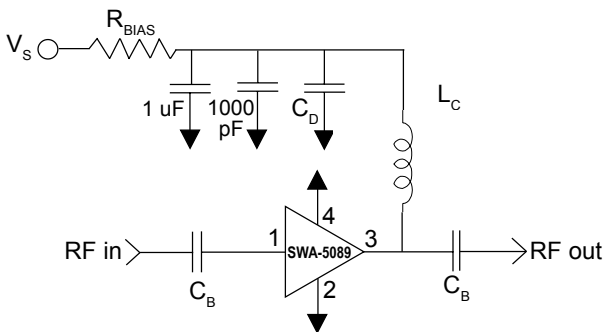
$|S_{12}|$ vs. Frequency



$|S_{22}|$ vs. Frequency

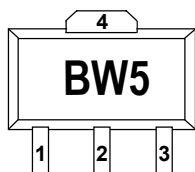


Basic Application Circuit (no tuning elements)



Part Identification Marking

The part will be marked with an "BW5" designator on the top surface of the package.



Caution: ESD sensitive

Appropriate precautions in handling, packaging and testing devices must be observed.

Application Circuit Element Values

Reference Designator	Frequency (Mhz)				
	500	850	1950	2400	3500
C _B	220 pF	100 pF	68 pF	56 pF	39 pF
C _D	100 pF	68 pF	22 pF	22 pF	15 pF
L _C	68 nH	33 nH	22 nH	18 nH	15 nH

Recommended Bias Resistor Values for I_b=80mA

$$R_{BIAS} = (V_S - V_D) / I_D$$

Supply Voltage(V _s)	7.5 V	8 V	10 V	12 V
R _{BIAS}	33 Ω	39 Ω	68 Ω	91 Ω

Note: R_{BIAS} provides DC bias stability over temperature.

Mounting Instructions

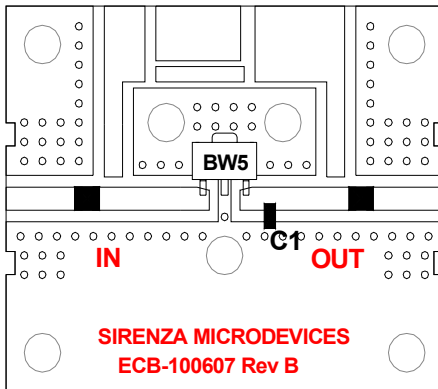
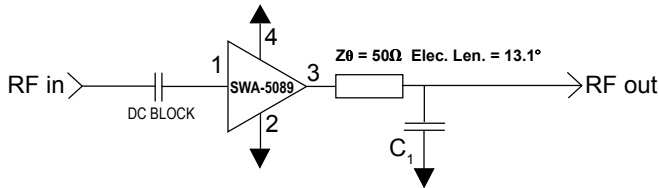
1. Solder the copper pad on the backside of the device package to the ground plane.
2. Use a large ground pad area with many plated through-holes as shown.
3. We recommend 1 or 2 ounce copper. Measurement for this data sheet were made on a 31 mil thick FR-4 board with 1 ounce copper on both sides.

Pin #	Function	Description
1	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.
2, 4	GND	Connection to ground. Use via holes for best performance to reduce lead inductance as close to ground leads as possible.
3	RF OUT/BIAS	RF output and bias pin. DC voltage is present on this pin, therefore a DC blocking capacitor is necessary for proper operation.

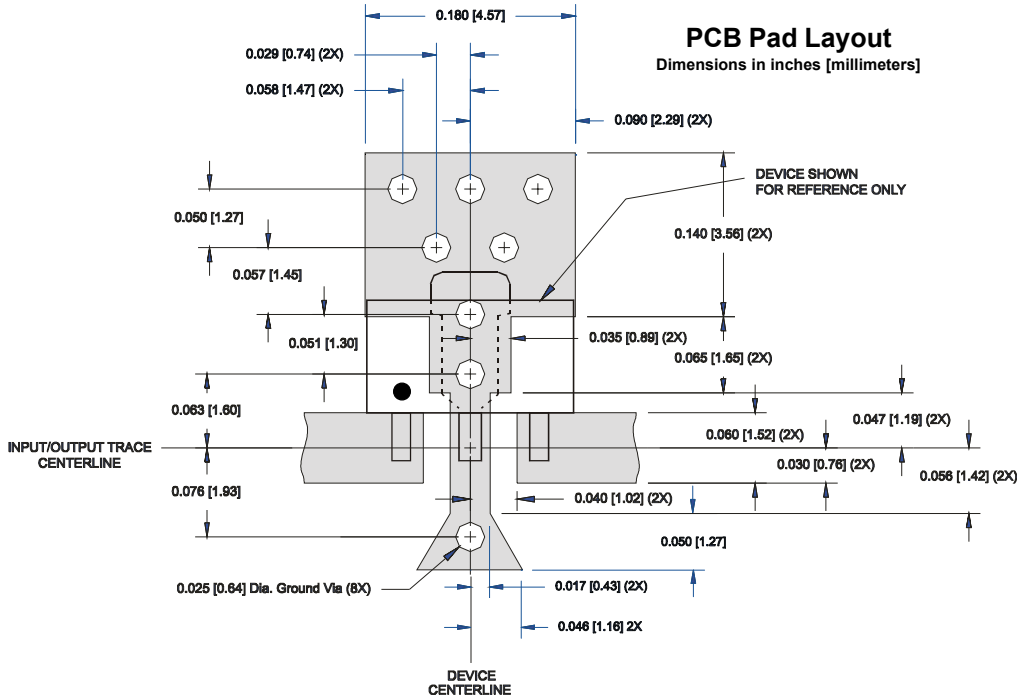
Part Number Ordering Information

Part Number	Reel Size	Devices/Reel
SBW-5089	7"	1000

Application Circuit with 5 - 8GHz tuning and broadband bias tee



C1 = 0.1pF 0805 AVX
 Substrate Material = Getek ML200C,
 0.031" thick, Er = 4.2, 1oz. cladding



Nominal Package Dimensions

Dimensions in inches [millimeters]

Refer to package drawing posted at www.sirenza.com for tolerances.

